

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4	CMOS with DMOS with photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/04 12:41
L2	5	DMOS same CMOS same photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/04 12:45
L3	115878	DMOS same CMOS same2 photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/04 12:45
L4	5	DMOS same CMOS same photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/04 12:45
L5	23	DMOS same CMOS and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/04 12:45
L6	4	DMOS same CMOS same implant\$4 and photodiode with implant\$4	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/01/04 12:46

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L7	4	DMOS same CMOS and photodiode with implant\$4	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 12:46
L8	16	DMOS same CMOS and photodiode and implant\$4	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 13:31
L9	8	"6331873"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 13:41
L10	2078	Double adj diffused with ((metal adj oxide) or "MOS" or "DMOS" or "DDMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:25
L11	568	10 and CMOS	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 13:42
L12	10	11 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:27

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L13	9	12 and silicon	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:19
L14	1230	257/292.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:19
L15	1021	257/336.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:19
L16	294	257/337.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:20
L17	677	257/499.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:20
L18	477	257/500.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:20

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L19	683	257/365.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:20
L20	4	14 and Double adj diffused with ((metal adj oxide) or "MOS" or "DMOS" or "DDMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:21
L21	88	15 and Double adj diffused with ((metal adj oxide) or "MOS" or "DMOS" or "DDMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:21
L22	36	16 and Double adj diffused with ((metal adj oxide) or "MOS" or "DMOS" or "DDMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:21
L23	8	17 and Double adj diffused with ((metal adj oxide) or "MOS" or "DMOS" or "DDMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:22
L24	26	18 and Double adj diffused with ((metal adj oxide) or "MOS" or "DMOS" or "DDMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:22

EAST Search History

L25	19	19 and Double adj diffused with ((metal adj oxide) or "MOS" or "DMOS" or "DDMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:22
L26	1	20 and complementary with ((metal adj oxide) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:22
L27	11	21 and complementary with ((metal adj oxide) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:23
L28	2	22 and complementary with ((metal adj oxide) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:23
L29	2	23 and complementary with ((metal adj oxide) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:23
L30	2	24 and complementary with ((metal adj oxide) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:23

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L31	1	25 and complementary with ((metal adj oxide) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:26
L32	1	26 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:23
L33	1	27 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:24
L34	1	28 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:24
L35	1	29 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:24
L36	1	30 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:24

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L37	1	31 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:24
L38	212	10 and complementary with ((metal adj oxide) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:24
L39	911932	((Double adj diffused with (metal adj oxide)) or "MOS" or "DMOS" or "DDMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:31
L40	54621	39 and ((complementary with (metal adj oxide)) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:26
L41	3318	40 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:27
L42	25874	((Double adj diffused with (metal adj oxide)) or "MOS" or "DMOS" or "DDMOS") same ((complementary with (metal adj oxide)) or "CMOS")	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:27

EAST Search History

L43	740	((Double adj diffused with (metal adj oxide)) or "MOS" or "DMOS" or "DDMOS") same ((complementary with (metal adj oxide)) or "CMOS") same photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:28
L44	389	((Double adj diffused with (metal adj oxide)) or "MOS" or "DMOS" or "DDMOS") with ((complementary with (metal adj oxide)) or "CMOS") with photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:30
L45	4	((Double adj diffused) with ((metal adj oxide) or "MOS") or "DMOS" or "DDMOS") with ((complementary with (metal adj oxide)) or "CMOS") with photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 14:31
S1	19	CMOS and (field adj oxide or "FOX") and (high adj voltage with well) and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:01
S2	12	S1 and double adj diffus\$4	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 06:51
S3	4	S2 and SOI	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2008/01/04 12:40

EAST Search History

S4	30	("3207510" "5242841" "5498554" "5519247" "5844264" "5933731" "6090652" "6130458" "6258701" "6444487" "6546798" "6580138" "6686233" "6713347").PN.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:01
S5	4	S4 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:03
S6	0	SOI and FO and (high adj voltage with well) and (low adj voltage with well) and source and drain and contact	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:04
S7	4	SOI and FOX and (high adj voltage with well) and (low adj voltage with well) and source and drain and contact	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:08
S8	1	SOI and FOX and (high adj voltage with region) and (low adj voltage with region) and source and drain and contact	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:05
S9	13	SOI and FOX and (high adj voltage) and (low adj voltage) and source and drain and contact	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:05

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S10	531	(high adj voltage with well) and (low adj voltage with well) and source and drain and contact	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:11
S11	210	S10 and field adj oxide	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:08
S12	0	S11 and silicon adj on adj insulator	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:08
S13	162	S11 and substrate with silicon	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:09
S14	123	S13 and MOS	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:09
S15	58	S14 and MOSFET	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:09

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S16	0	S11 and photodiode and FET	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:09
S17	0	S11 and photodiode and MOS	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:09
S18	0	S11 and photodiode and MOSFET	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:10
S19	89	S11 and MOSFET	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:10
S20	28	(high adj voltage adj well) and (low adj voltage adj well) and source and drain and contact	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:36
S21	4	S20 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:15

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S22	748	438/527.ccls.	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:15
S23	12	S22 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:15
S24	54542	"20" and SOI	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:35
S25	8	(high adj voltage adj well) and (low adj voltage adj well) and source and drain and contact and SOI	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:40
S26	8180	CMOS and SOI	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:41
S27	487	S26 and photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:42

EAST Search History

S28	7	S27 and double adj diffus\$4	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:41
S29	6	("6040593" "6194258" "6306678" "6323054" "6347054" "6486521").PN.	US-PGPU B; USPAT; USOCR	OR	OFF	2005/10/07 07:42
S30	63	S26 and photodiode and substrate with single adj crystal	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:49
S31	16	S30 and high adj voltage and low adj voltage	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:45
S32	487	photodiode and CMOS and SOI	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:50
S33	66	photodiode and CMOS and SOI and single adj crystal adj silicon	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:50
S34	41	photodiode and CMOS and SOI and single adj crystal adj silicon and source and drain	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:56

EAST Search History

S35	13	photodiode and CMOS and SOI and single adj crystal adj silicon and source and drain and well same high adj voltage	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:50
S36	43	photodiode and CMOS and SOI and single adj crystal adj silicon and p adj type	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2005/10/07 07:56
S37	11	"5477065"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/02/14 16:55
S38	3	"5477065" and double with diffus\$4 with MOS	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/02/14 17:26
S39	6	DMOS same CMOS same ("PD" or photodiode)	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/02/14 17:27
S40	0	DMOS same CMOS same ("PD" or photodiode) same implantation	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/02/14 17:27

EAST Search History

S41	4	DMOS same CMOS same ("PD" or photodiode) same dop\$4	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/02/15 12:45
S42	21	"5360748"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/02/14 17:31
S43	3	"6861341"	US-PGPU B; USPAT; USOCR; FPRS; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/02/15 12:45
S44	4	CMOS with DMOS with photodiode	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/11/23 20:58
S45	13	"5477065"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/11/23 21:14
S46	25	"6323534"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/11/23 21:22

EAST Search History

S47	9	S46 and (LOCOS or STI)	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/11/23 21:29
S48	5	"6358813"	US-PGPU B; USPAT; USOCR; EPO; JPO; DERWEN T; IBM_TDB	OR	ON	2007/11/23 21:29